

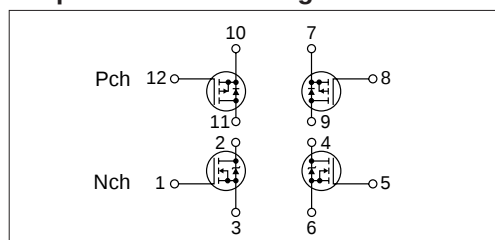
Absolute maximum ratings

(Ta=25°C)

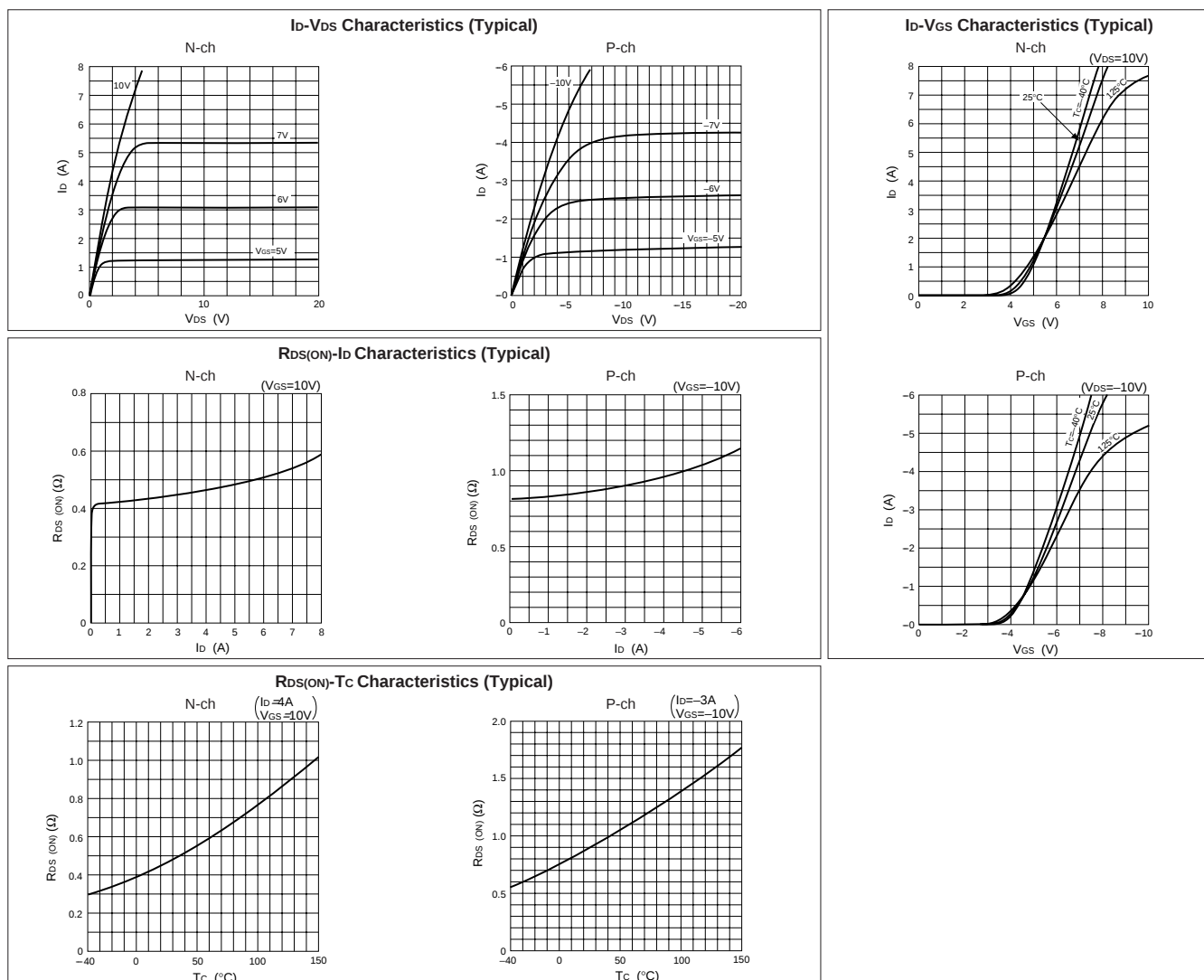
Symbol	Ratings		Unit
	N channel	P channel	
V _{DSS}	100	-100	V
V _{GSS}	±20	±20	V
I _D	±4	±3	A
I _{D(pulse)}	±8 (PW≤1ms)	±6 (PW≤1ms)	A
E _{AS} *	15	—	mJ
P _T	5 (Ta=25°C, with all circuits operating, without heatsink)		W
	35 (Tc=25°C, with all circuits operating, with infinite heatsink)		W
θ _{j-c}	3.57		°C/W
V _{ISO}	1000 (Between fin and lead pin, AC)		V _{rms}
T _{ch}	150		°C
T _{stg}	-40 to +150		°C

*: V_{DD}=20V, L=1mH, I_D=5A, unclamped, see Fig. E on page 15.

Equivalent circuit diagram



Characteristic curves



Electrical characteristics

($T_a=25^\circ\text{C}$)

Symbol	N channel					P channel				
	Specifications			Unit	Conditions	Specifications			Unit	Conditions
	min	typ	max			min	typ	max		
V _{(BR)DSS}	100			V	I _D =250μA, V _{GS} =0V	−100			V	I _D =−250μA, V _{GS} =0V
I _{GSS}			±500	nA	V _{GS} =±20V			±500	nA	V _{GS} =±20V
I _{DSS}			250	μA	V _{DS} =100V, V _{GS} =0V			−250	μA	V _{DS} =−100V, V _{GS} =0V
V _{TH}	2.0		4.0	V	V _{DS} =10V, I _D =250μA	−2.0		−4.0	V	V _{DS} =−10V, I _D =−250μA
R _{E(yfs)}	1.1	1.7		S	V _{DS} =10V, I _D =4A	0.7	1.1		S	V _{DS} =−10V, I _D =−3A
R _{DS(ON)}		0.50	0.60	Ω	V _{GS} =10V, I _D =4A		1.1	1.3	Ω	V _{GS} =−10V, I _D =−3A
C _{ISS}		180		pF	V _{DS} =25V, f=1.0MHz,		180		pF	V _{DS} =−25V, f=1.0MHz,
C _{OSS}		82		pF	V _{GS} =0V		85		pF	V _{GS} =0V
t _{on}		40		ns	I _D =4A, V _{DD} ÷50V, V _{GS} =−10V,		90		ns	I _D =−3A, V _{DD} ÷50V, V _{GS} =−10V,
t _{off}		40		ns	see Fig. 3 on page 16.		80		ns	see Fig. 4 on page 16.
V _{SD}		1.2	2.0	V	I _{SD} =4A		−4.0	−5.5	V	I _{SD} =−3A
t _{rr}		250		ns	I _{SD} =±100mA		250		ns	I _{SD} =±100mA

■ Characteristic curves

